



40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET **POWERDI**

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D T _C = +25°C
40V	$10m\Omega$ @ $V_{GS} = 10V$	80A

Description

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Engine Management Systems
- **Body Control Electronics**
- **DCDC** Converters

Features

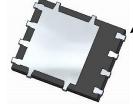
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching ensures more reliable and robust end application
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- Low Input Capacitance
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMNH4011SPSQ)

Mechanical Data

- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

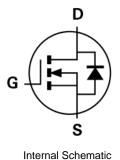


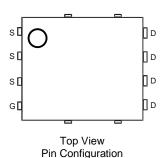
Top View



Bottom View







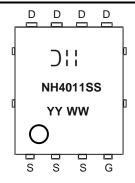
Ordering Information (Note 4)

Part Number	Case	Packaging	
DMNH4011SPS-13	PowerDI5060-8	2,500 / Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



) | | = Manufacturer's Marking NH4011SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016)WW = Week (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	40	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (V _{GS} = 10V) (Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	13 10.8	А
Continuous Drain Current (V _{GS} = 10V) (Note 7)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	80 57	А
Maximum Continuous Body Diode Forward Current (Note	I _S	80	Α	
Pulsed Drain Current (10μs pulse, duty cycle = 1%)		I _{DM}	90	Α
Avalanche Current, L = 1mH (Note 8)		I _{AS}	18	Α
Avalanche Energy, L = 1mH (Note 8)		E _{AS}	170	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P_{D}	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ hetaJA}$	99	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P_D	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	60	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	P_D	100	W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	1.5	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

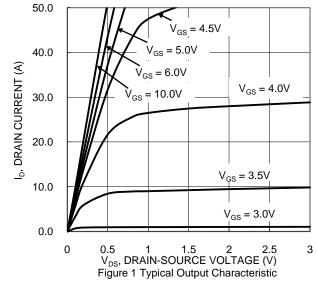
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	1	_	1	μΑ	$V_{DS} = 40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	2	_	4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		8.5	10	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	V_{SD}	1	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}		1405			V _{DS} = 20V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss		247	_	pF		
Reverse Transfer Capacitance	C _{rss}		108	_			
Gate Resistance	R_g		2.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	25.5	_			
Gate-Source Charge	Q _{gs}	_	4.6	_	nC	$V_{DS} = 20V, V_{GS} = 10V, I_{D} = 50A$	
Gate-Drain Charge	Q _{gd}	_	6.9	_			
Turn-On Delay Time	t _{D(ON)}	_	4.6	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 50A, R_{G} = 3.5\Omega$	
Turn-On Rise Time	t _R	_	3.7	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	16	_	ns		
Turn-Off Fall Time	t _F	_	5.1	_			
Body Diode Reverse Recovery Time	t _{RR}	_	22.1		ns	I 500 di/dt 1000/up	
Body Diode Reverse Recovery Charge	Q _{RR}	1	13.4	_	nC	$I_F = 50A$, di/dt = 100A/ μ s	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







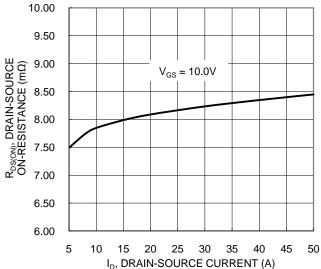


Figure 3 Typical On-Resistance vs Drain Current and Gate Voltage

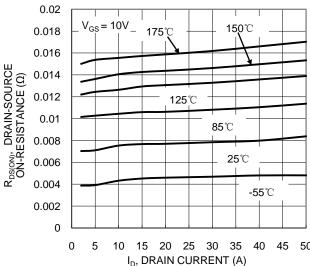
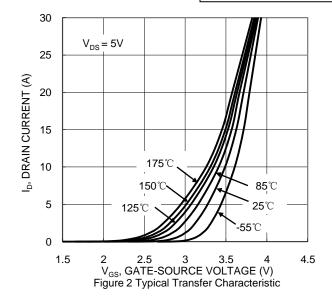
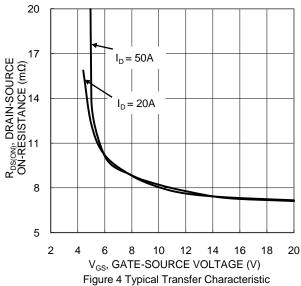


Figure 5 Typical On-Resistance vs Drain Current and Temperature





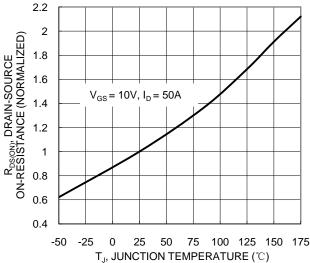
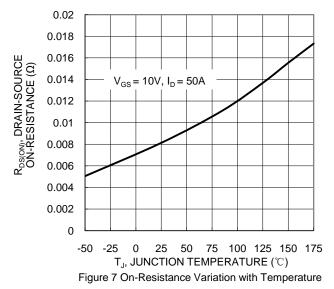


Figure 6 On-Resistance Variation with Temperature



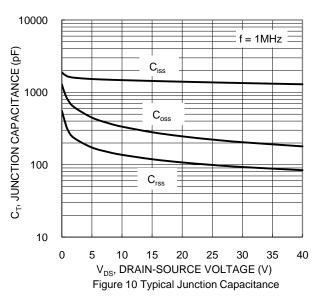


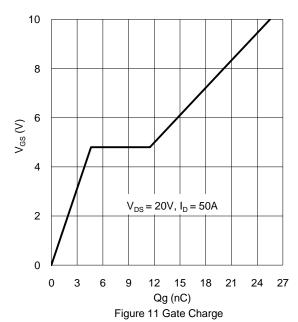


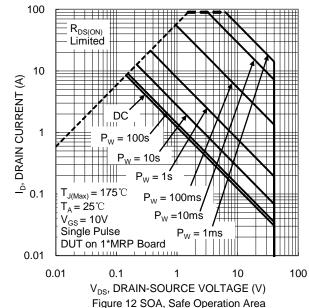
 $V_{\text{GS(TH)}}$, GATE THRESHOLD VOLTAGE (V) 2.8 2.6 2.4 $I_D = 1mA$ 2.2 2 1.8 $I_{D} = 250 \mu A$ 1.6 1.4 1.2 -50 25 50 75 100 125 150 175 T_J , JUNCTION TEMPERATURE ($^{\circ}$ C) Figure 8 Gate Threshold Variation vs Temperature

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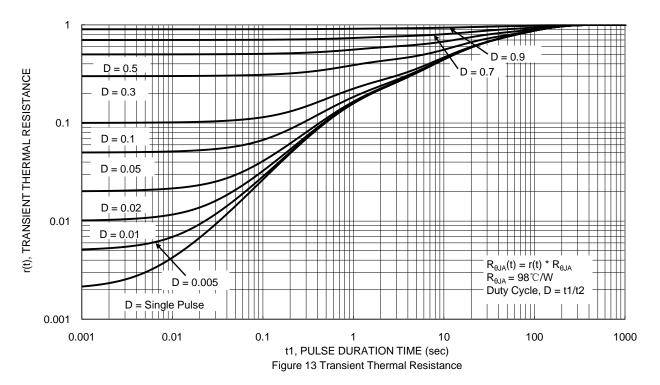
50 43 Is, SOURCE CURRENT (A) 36 29 T_A = 175°C 22 = 150°C 15 T_A = 85°C T_A = 125℃ T_A = 25℃ 8 = -55°C 1 0 0.6 1.2 0.3 0.9 1.5 V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9 Diode Forward Voltage vs Current









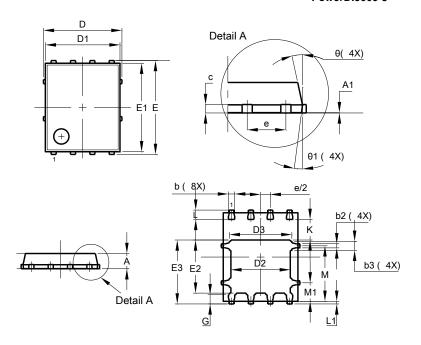




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

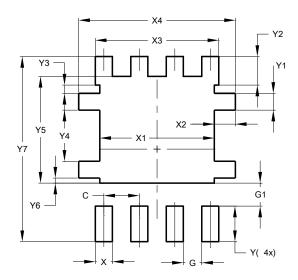


PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A 1	0.00	0.05		
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
C	0.230	0.330	0.277	
D	,	5.15 BSC		
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
Е	(6.15 BSC		
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е		1.27 BSC		
G	0.51	0.71	0.61	
K	0.51			
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
M	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12º	11º	
Θ1	6°	80	7°	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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